# IEEE 10BASE-T1S EMC Test Specification for Common Mode Chokes

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This EMC measurement specification shall be used as a standardized common scale for EMC evaluation of common mode chokes for 10BASE-T1S applications.

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# Contents

Fo	rewoi	r <mark>d (Di</mark> s	sclaimer)	5
Int	roduc	ction .		8
Ab	brevi	ation/	/Symbols	8
1	Sco	pe		9
2	No	rmativ	ve references	9
3	Ter	ms ar	nd Definitions	9
4	Gei	neral.		10
5	Tes	st and	measurement	10
	5.1	Gen	eral definitions	10
	5.2	Mea	asurement of parasitic capacitance	11
	5.2	.1	VNA measurement method	11
	5.2	.1.1	Test setup	11
	5.2	.1.2	Test procedure and parameters	12
	5.2	.2	LCR meter or impedance analyzer measurement method	14
	5.2	.2.1	Test setup	14
	5.2	.2.2	Test procedure and parameters	14
	5.3	S-pa	arameter measurement mixed mode	16
	5.3	.1	Test setup	16
	5.3	.2	Test procedure and parameters	19
	5.4	ESD	damage	22
	5.4	.1	Test setup	22
	5.4	.2	Test procedure and parameters	24
	5.5	Satu	uration test at RF disturbances	26
	5.5	.1	Test setup	26
	5.5	.2	Test procedure and parameters	27
	5.6	Satu	uration test at ESD	29
	5.6	.1	Test setup	29
	5.6	.2	Test procedure and parameters	30
An	inex A	Reco	mmended limits for tests	33

A.1	Parasitic capacitance	33
A.2	S-parameter measurement mixed mode	34
A.3	ESD damage	36
A.4	Saturation test at RF disturbances	36
A.5	Saturation test at ESD	37
Annex B	Correction methods for usage of DUT connection cable longer than 0.1 m for TPL measurements	38
B.1	Reference time correction procedure	38

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# Introduction

The IEEE 802.3cg standard defines a 10 Mbit/s Ethernet communication over an unshielded single pair of conductors and separate the two systems 10BASE-T1S and 10BASE-T1L. The 10BASE-T1S implementation covers a half duplex communication using a CSMA/CD for point to point channel and the optional functionalities full duplex communication for a point to point channel and a half duplex communication for a so called mixing segment (or multidrop mode) with at least 8 nodes and 25 m length of bus lines. In any case, the bus cable is terminated with the line impedance of 100  $\Omega$  at both ends of the channel. As an optional feature to enable a deterministic access time for each bus node in a mixing segment the new access method PLCA is overlaid to the CSMA/CD system.

Due to the high communication rate of 10BASE-T1 and the intended use of unshielded twisted pair cable, a high risk of EMC problems is expected. For this reason, an EMC optimization of all components of the Ethernet physical layer is required.

A CMC is used as part of a 10BASE-T1S MDI interface circuit and has a strong impact to the functional and EMC behavior of the complete system. This EMC measurement specification is focused on evaluation of the CMC characteristics related to high frequency and functional aspects as well as ESD.

# **Abbreviation/Symbols**

CDMR	Common to Differential Mode Rejection, common mode single ended measured
CMC	Common Mode Choke
DCMR	Differential to Common Mode Rejection, common mode single ended measured
IL	Insertion Loss
RF	Radio Frequency
RL	Return Loss
S-Parameter	Scattering Parameter
VNA	Vector Network Analyzer
TLP	Transmission Line Pulse

# 1 Scope

This document specifies test and measurement methods for characterization of CMCs intended to be used for Ethernet interfaces for 10BASE-T1S. It contains definitions for test methods, test conditions, performance criteria, test procedures, test setups, test boards and recommended limits and covers

- parasitic capacitance;
- S-parameter measurement mixed mode;
- ESD damage test;
- saturation test at RF disturbances;
- saturation test at ESD.

This document does not cover devices that are intended for use in power over data line applications.

# 2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

- [1] IEEE P802.3cg<sup>™</sup>: Physical Layer Specifications and Management Parameters for 10 Mb/s Operation and Associated Power Delivery over a Single Balanced Pair of Conductors
- [2] IEC 62615, Electrostatic discharge sensitivity testing Transmission line pulse (TLP) Component level
- [3] ISO 10605, Road vehicles Test methods for electrical disturbances from electrostatic discharge

# **3** Terms and Definitions

For the purposes of this document, the terms and definitions given in 2 and following apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- ISO Online browsing platform: available at https://www.iso.org/obp;
- IEC Electropedia: available at <u>http://www.electropedia.org.</u>

# 4 General

The intention of this document is to evaluate the EMC performance of CMCs intended to use for 10BASE-T1S Ethernet interfaces. The final judgment of the tested device is left to the customer.

# 5 Test and measurement

# 5.1 General definitions

All tests are performed for standard room temperature (23 °C +/- 3 K).

In general, a printed circuit board with RF board-to-coax connectors should be used for all tests. To ensure reliable RF parameters, a test board with at least two layers with enlarged GND reference plane is required. The traces on the test board should be designed as 50 ( $\pm$  5)  $\Omega$  single ended transmission lines with a length as short as possible. For design of CMC footprint and the definition of minimal distance of CMC housing and CMC terminals to the GND plane the related specification of CMC manufacturer should be used, if not otherwise specified in the specific tests.

The test board design and the method of connecting the CMC with the test board is intended to provide high accuracy and reproducible test results and is with more details described in the respective measurement chapters.

A general electrical drawing with winding and pin definitions of a CMC is shown in Figure 5-1.



Figure 5-1: General electrical drawing of a CMC

For the measurements described below the CMC line 1 is defined as the CMC winding between pin 1 and pin 2 and line 2 is defined as the winding between pin 3 and pin 4.

# 5.2 Measurement of parasitic capacitance

#### 5.2.1 VNA measurement method

#### 5.2.1.1 Test setup

The test setup for measuring the parasitic capacitance consists of a VNA in combination with a special test board (adapter test board). The test board is included into the test setup during VNA calibration. The reference points for calibration are defined to the pads of CMC pins 1 and 3 at the test board.



Vector network analyzer

#### Figure 5-2: Test setup for parasitic capacitance measurement for VNA method

The test equipment definitions are the following:

- vector network analyzer;
- test board parasitic capacitance .

The connecting traces of the test board from RF connectors to CMC pins 1 and 3 should be routed symmetrically at 45° to decrease parasitic inductive coupling. The CMC pins 2 and 4 are unconnected. An example for test board is given in Figure 5-3.



## Figure 5-3: Example of test board parasitic capacitance measurement for VNA method, top layer

The test board symmetry and calibration accuracy should be validated with measurement of an open-circuit (without DUT). The remaining open-circuit capacitance should not exceed 500 fF.

#### 5.2.1.2 Test procedure and parameters

The test procedure and parameters are defined in Table 5-6.

ltem	Parameter		
Frequency range:	1 MHz to 100 MHz		
S-parameter per single path:	S <sub>11</sub> , Re + j lm / CMC pin 1 S <sub>22</sub> , Re + j lm / CMC pin 3		
	$S_{21}$ , Re + j Im / CMC pin 1 to pin 3		
	$S_{12}$ , Re + j Im / CMC pin 3 to pin 1		
VNA measurement	port definitions:		
circuit:	logic port 1: physical port 1 / CMC pin 1		
	logic port 2: physical port 2 / CMC pin 3		
	$\begin{array}{c} \text{Test board} \\ \text{Logical port 1} \\ \text{VNA port 1 (50 \Omega)} \\ \text{Logical port 2} \\ \text{VNA port 2 (50 \Omega)} \end{array}$		

Calculation method:	1.	Calculate Y-Parameters from S-Parameters: $\begin{bmatrix} S \end{bmatrix} = \begin{bmatrix} s_{11} & s_{12} \\ s_{21} & s_{22} \end{bmatrix} \implies \begin{bmatrix} Y \end{bmatrix} = \begin{bmatrix} Y_{11} & Y_{12} \\ Y_{21} & Y_{22} \end{bmatrix}$	
		NOTE All calculations should be performed using raw or linearly interpolated data, to avoid inaccuracy introduced by e.g. spline interpolation or rational fitting.	
	2.	Calculate the mean transfer Y-Parameter $Y_{T}$ :	
		$Y_T = \frac{(Y_{21} + Y_{12})}{2} = \frac{S_{12} + S_{21}}{50 \cdot (1 + S_{11} - S_{12} \cdot S_{21} + S_{22} + S_{11} \cdot S_{22})}$	
	3.	Calculate the parasitic capacitance $C_{para}(f)$ while extracting the negative imaginary part of $Y_T$ : $C_{para}(f) \approx \frac{Im(-Y_T)}{2\pi f}$	
	4.	The resulting value $C_{para_max}$ is the maximum value of $C_{para}$ (f) in the frequency range from f = 5 MHz to f = 15 MHz.	

# Table 5-1: Test procedure and parameters for parasitic capacitance measurements at CMC using VNA method

The tests should be performed at 10 samples and documented in a diagram with  $C_{para}$  (f) and  $C_{para_max}$  according to the scheme given in Table 5-2. Recommended limits for evaluation are given in A.1.

Test	ltem	Sample
CP1	$C_{para\_max}$	10 samples

Table 5-2: Required	l parasitic capacitance	measurements for CMC
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#### 5.2.2 LCR meter or impedance analyzer measurement method

#### **5.2.2.1** Test setup

The test setup for measuring the parasitic capacitance consists of a LCR meter or an impedance analyzer in combination with a special test fixture extension, direct mounted to the measuring device. The reference points for calibration are defined to the pads of CMC pins 1 and 3 at the test board.



LCR meter or impedance analyzer

#### Figure 5-4: Test setup for parasitic capacitance measurement for LCR meter or impedance analyzer method

The test equipment definitions are the following:

- LCR meter or impedance analyzer;
- test fixture extension, direct mounted to the measuring device .

#### 5.2.2.2 Test procedure and parameters

The test procedure and parameters are defined in Table 5-6.

ltem	Parameter
Test frequency:	5 MHz
LCR meter or impedance analyzer setting:	Cs
LCR or impedance analyzer measurement circuit:	Terminal

# Table 5-3: Test procedure and parameters for parasitic capacitance measurements at CMC using LCR meter or impedance analyzer method

The tests should be performed at 10 samples and documented. Recommended limits for evaluation are given in A.1.

Test	ltem	Sample
CP1	$C_{para\_max}$	10 samples

#### Table 5-4: Required parasitic capacitance measurements for CMC

# 5.3 S-parameter measurement mixed mode

#### 5.3.1 Test setup

The test setup for measuring the mixed mode *S*-parameters consists of a 4-port VNA in combination with a special test board (adapter test board). The test board is included into the test setup during VNA calibration. The reference points for calibration are defined to the pads of the CMC at the test board.



Vector network analyzer

#### Figure 5-5: Test setup for S-parameter measurements

The test equipment definitions are the following:

- 4-port vector network analyzer;
- test board S-parameter mixed mode (4-port);
- test board S-parameter single ended (3-port).

For the *S*-parameter 3-port test board, additional specific requirements are defined. The 3-port test board with soldered RF connectors used for balance measurement should have a very high grade of self-balance. To ensure the test board self-balance characteristic of symmetrical network at logical port 2 (common mode), the traces between the DUT and all resistors (R1, R2 and R3) must be kept highly symmetric and as short as possible. To verify the test board self-balance characteristic, the test parameter and requirements given in Table 5-5are defined.

Examples for test boards are given in Figure 5-6 and Figure 5-7.



Figure 5-6: Example of test board 4-port S-parameter measurement at CMC – mixed mode, top layer



Figure 5-7: Example of test board 3-port S-parameter measurement at CMC – single ended, top layer

The reference points for calibration are the pads of the CMC footprint at the test board.



Table 5-5: Test procedure and parameters for 3-port test board characterization for CMC

### 5.3.2 Test procedure and parameters

Item	Parameter	
Frequency range:	0.3 MHz to 1 GHz	
S-parameter per single path:	4-port parameters $S_{dd11}$ (RL), logarithmic magnitude in dB / CMC orientation 1 $S_{dd22}$ (RL), logarithmic magnitude in dB / CMC orientation 2 $S_{dd21}$ (IL), logarithmic magnitude in dB $S_{cc21}$ (CMR), logarithmic in dB3-port parameters $S_{d21}$ (DCMR), logarithmic magnitude in dB / CMC orientation 1 $S_{sd12}$ (DCMR), logarithmic magnitude in dB / CMC orientation 2 $S_{ds12}$ (DCMR), logarithmic magnitude in dB / CMC orientation 1 $S_{ds12}$ (DCMR), logarithmic magnitude in dB / CMC orientation 2 $S_{ds12}$ (CDMR), logarithmic magnitude in dB / CMC orientation 1 $S_{ds12}$ (CDMR), logarithmic magnitude in dB / CMC orientation 2For $S_{sd12}$ and $S_{ds12}$ measurement the terminal orientation of the CMC isrotated by 180° on the test board.	
VNA measurement circuit:	port definitions: mixed mode logic port 1: physical port 1a and port 1b mixed mode logic port 2: physical port 2a and port 2b pin 1 of CMC is placed on logic port 1. 4-port measurements / $S_{dd11}$ , $S_{dd22}$ , $S_{dd21}$ and $S_{cc21}$ mixed mode: 50 $\Omega$ input impedance at each measurement port Test board VNA port 1a Logical port 1 VNA port 1b (50 $\Omega$ ) Logical port 1 VNA port 1b (50 $\Omega$ )	

The test procedure and parameters are defined in Table 5-6.



Table 5-6: Test procedure and parameters for S-parameter measurements at CMC

The measurements should be performed and docum	nented according to the scheme given in Table 5-7.
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Test	S-parameter	Reference impedance differential mode ª	Reference impedance common mode ª	Sample
S1a	S <sub>dd11</sub> (RL)	100 Ohm	25 Ohm	
S1b <sup>b</sup>	S <sub>dd11</sub> (RL)	50 Ohm	12.5 Ohm	
S2a	S <sub>dd22</sub> (RL)	100 Ohm	25 Ohm	
S2b <sup>b</sup>	S <sub>dd22</sub> (RL)	50 Ohm	12.5 Ohm	
S3	S <sub>dd21</sub> (IL)	100 Ohm	25 Ohm	
S4	S <sub>cc21</sub> (CMR)	100 Ohm	25 Ohm	10 samples each
S7	S <sub>sd21</sub> (DCMR)	100 Ohm	25 Ohm	
S8	S <sub>sd12</sub> (DCMR)	100 Ohm	25 Ohm	
S9	S <sub>ds21</sub> (CDMR)	100 Ohm	25 Ohm	
S10	S <sub>ds12</sub> (CDMR)	100 Ohm	25 Ohm	
<ul> <li><sup>a</sup> for S1 to S4: definition valid for physical port 1a, 1b, 2a and 2b</li> <li>for S7 to S10: definition valid for physical port 1a, 1b, physical port 2a is defined to 50 Ohm</li> <li>for single ended</li> <li><sup>b</sup> renormalization of measured results for 100 Ohm differential mode and 25 Ohm common</li> </ul>				
mode im impedar	mode impedance condition into 50 Ohm differential mode and 12.5 Ohm common mode impedance condition			

#### Table 5-7: Required S-parameter measurements for CMC

For each test case, the results for all 10 samples should be documented as diagram in the CMC characterization report. Recommended limits for evaluation are given in Annex A.2.

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#### 5.4 ESD damage

#### 5.4.1 Test setup

The test setup given in Figure 5-8 is used for testing the ESD robustness of CMC.



Figure 5-8: Test setup for ESD damage tests at CMC

The test equipment definitions are the following:

- ESD generator (according to ISO 10605, discharge storage capacitor C = 150 pF and discharge resistor R = 330 Ω);
- ESD test board;
- ground plane;
- test board fixture.

The ground plane with a minimum size of  $0.5 \text{ m} \times 0.5 \text{ m}$  is connected to protective earth of the electrical grounding system of the test laboratory. The ESD generator ground return cable is directly connected to this ground plane.

The metallic test fixture positions the ESD test board and directly connects the ESD test board ground plane to the reference ground plane. The ground connection of the test fixture is connected to ground plane with low impedance and low inductance. This surface connection should have a contact area of at least 4 cm<sup>2</sup>. Copper tapes can be used in addition.

For testing the tip of the ESD generator is directly contacted with one of the discharge points DP1 and DP2 of the ESD test board. For this purpose, the discharge points are implemented as rounded vias in the layout of the ESD test board and are directly connected by a trace 15 (±5) mm with the respective pin of the CMC.

To achieve a high grade of accuracy of required S-parameter measurements for damage evaluation, it is recommended to use the same test board for S-parameter and ESD tests without re-soldering the DUT. For check of damage evaluation criteria (S-parameter), the reference points for calibration are the input of RF connector (SMA) at the test board.



An example for ESD test board is given in Figure 5-9.

Figure 5-9: Example of ESD test board for CMC, top layer

NOTE While using the ESD test board example given in Figure 5-9 the serial jumpers JP1 and JP2 are left open and the resistors R1 and R2 are populated for ESD tests itself. For S-parameter measurement, the jumpers JP1 and JP2 are closed and the resistors R1 and R2 are not populated. The purpose of using jumpers JP1 and JP2 is to avoid parasitic discharge (ESD spark over event) from discharge points DP1 and DP2 to the ground plane of the ESD test board that can occur at the RF connector (SMA) because of the small dimensions at the connector contacts.

Other test board implementations without using jumpers to disconnect the discharge points from the RF connector terminal can be used as well (e.g. de-soldering the RF connector from ESD test board for ESD test itself). However, in all cases, the avoidance of parasitic discharge from discharge points DP1 and DP2 to the ground plane needs to be checked before testing for unpopulated CMC with a maximum ESD test voltage of +/-8 kV.

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#### 5.4.2 Test procedure and parameters

The required tests and procedure are defined in Table 5-8 and should be done on one sample.

Item	Parameter		
Coupling of ESD:	Direct discharge method according to ISO 10605 (discharge storage capacitor C = 150 pF and discharge resistor R = 330 $\Omega$ )		
Test circuit:	Test board $DP1 \qquad \qquad$		
ESD test voltage:	± 8 kV		
Number of discharges:	10 per polarity		
Time between discharges:	5 s		
Damage evaluation criteria:	<ul> <li>degrade by more than 0,1 dB from the initial value after performing the tests for S-parameter S<sub>dd21</sub> for frequencies f ≤ 200 MHz</li> <li>degrade by more than 1 dB from the initial value after performing the tests for S-parameter S<sub>dd11</sub>, S<sub>dd22</sub> and S<sub>cd21</sub> for frequencies f ≤ 200 MHz</li> <li>The S-parameter measurements should be done according to 5.3. Frequency ranges or frequency spots with a level at noise floor or below the related limits of 5.3 should not be weighted for applying the damage evaluation criteria.</li> <li>For simplification of measurement for check of mode conversion loss the S-parameter S<sub>cd21</sub> is used instead of S<sub>sd21</sub>. The setup for S-parameter S<sub>cd21</sub> is same as used for the other required S-parameter. Because of different test circuitry for S-parameter S<sub>cd21</sub> and S<sub>sd21</sub> the related limit for S-parameter S<sub>cd21</sub> is corrected by + 10 dB.</li> </ul>		
Test procedure:	<ol> <li>S-parameter reference measurement before ESD test</li> <li>apply ESD discharges at DP1 (± 8 kV, 10 per polarity, 5 s delay)</li> <li>apply ESD discharges at DP2 (± 8 kV, 10 per polarity, 5 s delay)</li> <li>demagnetization of CMC (if needed)</li> <li>evaluate damage using damage evaluation criteria</li> <li>If a damage occurs at ± 8 kV the test should be repeated with a reduced ESD test voltage to find out the immunity threshold of the DUT. Nevertheless, applying an ESD test voltage of ± 8 kV without damage for DUT is required to pass the test.</li> </ol>		

#### Table 5-8: Test parameters for ESD damage tests at CMC

Test	Discharge point	Comment	Sample
E1	DP1	Line 1	1 sample
E2	DP2	Line 2	i sample

The measurements should be performed and documented according to the scheme given in Table 5-9.

#### Table 5-9: Required ESD tests for damage for CMC

The CMC should withstand the ESD discharge without damage according to the damage evaluation criteria. Recommended limits are given in Annex A.3.

# 5.5 Saturation test at RF disturbances

#### 5.5.1 Test setup

The test setup for measuring the saturation effect at RF immunity tests consists of a 4-port VNA or 2-port VNA in combination with a RF amplifier, RF attenuator and a special test board. The test setup is given in Figure 5-10.



Vector network analyzer



The test equipment definitions are the following:

- 4-port or 2-port vector network analyzer;
- − RF amplifier (impedance 50  $\Omega$ , gain app. 40 dB, PCW ≥ 10 W);
- RF attenuator (impedance 50  $\Omega$ , attenuation 40 dB), and
- test board RF saturation / S-parameter (2-port).

An example for RF saturation / S-parameter test board is given in Figure 5-11.



Figure 5-11: Example of RF saturation / S-parameter test board for CMC, top layer

### 5.5.2 Test procedure and parameters

The required test procedure and parameters are defined in Table 5-10.

Item	Parameter	
Frequency range:	1 MHz to 1 GHz	
S-parameter power level:	$S_{21}$ (CMR), logarithmic magnitude in dB	
Measurement test circuit:	port definitions: logic port 1: physical port 1 logic port 2: physical port 2 line 1 of CMC is placed on transceiver side (logic port 1) $S_{21}$ measurement: 50 $\Omega$ input impedance at each measurement port Test board Single ended VNA port 1 (50 $\Omega$ ) CMC GDC CMC	
Test power level:	forward power: 24 dBm, 30 dBm, 33 dBm, 36 dBm These test levels are obtained from test level measurement into a 50 Ohm load.	
Dwell time per power level:	≥ 60 s	
Evaluation of saturation effect:	maximum deviation of 1 dB from the CMR reference value at 24 dBm for power level 30 dBm maximum deviation of 1 dB from the CMR reference value at 24 dBm for power level 33 dBm above 5 MHz maximum deviation of 1 dB from the CMR reference value at 24 dBm for power level 36 dBm above 7 MHz	
Test procedure:	<ol> <li>define the test equipment settings for test power levels 24 dBm, 30 dBm, 33 dBm and 36 dBm with replacement of DUT by short connections on the test board</li> <li>test with power level 24 dBm for setting the reference value</li> <li>test with power level 30 dBm and evaluation</li> <li>test with power level 33 dBm and evaluation</li> <li>test with power level 36 dBm and evaluation</li> </ol>	

Table 5-10: Test procedure and parameters for RF saturation tests at CMC

The tests should be performed at one sample and documented according to the scheme given in Table 5-11.

Test	S-parameter	Sample
RFS1	S <sub>21</sub> (CMR)	1 sample

#### Table 5-11: Required RF saturation tests for CMC

The CMC should withstand the RF power saturation test according to the evaluation criteria. Recommended limits are given in Annex A.4.

# 5.6 Saturation test at ESD

#### 5.6.1 Test setup

The test setup for measuring the saturation effect at ESD tests consists of a TLP test system, digital storage oscilloscope and a special test board. The test setup is given in Figure 5-12.



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#### Figure 5-12: Test setup for ESD saturation measurements at CMC

The test equipment definitions are the following:

- TLP test system according to IEC 62615, including TLP generator, current probe and voltage probe;
- DUT connection cable with length ≤ 0.1 m between the test board and the TLP voltage / current sense probes;
- digital storage oscilloscope (DSO, 50 Ω input impedance, minimum 4 GHz analog input bandwidth);
- test board CMC ESD saturation.

NOTE It is recommended to use a DUT connection cable with a maximum length of 0.1 m for lowering the parasitic impact of signal propagation delay to the definition of the reference time for the TLP measuring window  $t_0$  that can cause uncertainty in measuring results. If a DUT connection cable is used with more than 0.1 m length, the signal propagation delay on this cable needs to be considered for definition of the starting time for the TLP measuring window  $t_0$ . For this purpose a procedure is given in Annex B.

The TLP test system (including software for post procession, if available) shall be configured according to the definitions of TLP test system manufacturer. To ensure a correct implementation of all connection cables inside the TLP test system and to the DSO as well as the voltage and current probes, the complete system needs to be verified using calibration fixtures according to the definitions of IEC 62615 and the TLP test system manufacturer.



An example for CMC ESD saturation test board is given in Figure 5-13.



#### 5.6.2 Test procedure and parameters

The required test procedure and parameters are defined in Table 5-12.



Table 5-12: Test procedure and parameters for ESD saturation tests at CMC

The tests should be performed and documented according to the scheme given in Table 5-13.

Test	Discharge point	Comment	Parameter	Sample
ES1	DP1	Line 1	CMC ESD	
ES2	DP2	Line 2	saturation break down voltage	1 sample

Table 5-13: Required ESD saturation tests for CMC

For each test case, the TLP I/V characteristic should be recorded and documented in a diagram in the test report. The derived CMC ESD saturation break down voltage should be below the recommended limits given in Annex A.5.

# Annex A

# **Recommended limits for tests**

# A.1 Parasitic capacitance

Based on measurement result of parasitic capacitance  $C_{para_max}$  the CMC shall be classified using the definition of Table A-1.

Class	C <sub>para_max</sub>
I	13 pF < <i>C</i> <sub>para_max</sub> ≤ 17 pF
П	$10 \text{ pF} < C_{\text{para}_{max}} \le 13 \text{ pF}$
Ш	7 pF < $C_{\text{para}_{max}} \le 10$ pF
IV	C <sub>para_max</sub> ≤ 7 pF

Table A-1: Parasitic capacitance classes for CMC

An example of measurement results for typical CMCs using the VNA measurement method is shown in Figure A-1.



Figure A-1: Example of parasitic capacitance measurement results for CMC

# A.2 S-parameter measurement mixed mode

For evaluation of mixed mode S-Parameters the limits given in Figure A-2 to Figure A-5 are recommended. The required limit class depend on the application conditions and will be defined by the customer.



Figure A-2: Recommended characteristics for Sdd11, Sdd22 (RL) for CMC



Figure A-3: Recommended characteristics for Sdd21 (IL) for CMC







Figure A-5: Recommended characteristics for Ssd21, Ssd12 (DCMR) and Sds21, Sds12 (CDMR) for CMC

# A.3 ESD damage

It is recommended that the CMC must withstand the ESD discharge with discharge voltage amplitude of +/- 8 kV without damage.

# A.4 Saturation test at RF disturbances

It is recommended that the CMC must withstand the RF power saturation test according to the evaluation criteria up to power amplitude of 36 dBm.

# A.5 Saturation test at ESD

Based on measurement result of TLP I/V characteristic the CMC shall be classified using the definition of Table A-2 and Figure A-14.

Class	V <sub>ESD_br</sub>
I	50 V to 125 V
П	≥ 125 V

Table A-2: ESD saturation break down voltage classes for CMC

An example of measurement results for typical CMCs is shown in Figure A-14.



Figure A-14: Example of ESD saturation tests results for CMC

# Annex B

# Correction methods for usage of DUT connection cable longer than 0.1 m for TPL measurements

# **B.1** Reference time correction procedure

If a long DUT connection cable is used, the reflected wave observed on the TLP voltage and current sense probes - connected with the oscilloscope - will be delayed from the pulse output timing as shown in Figure B-1, resulting in current and voltage shapes being affected by the cable propagation delay. The time when the pulse arrives at the DUT is defined as the reference time t<sub>0</sub>, instead of the TLP pulse starting time, for the measurement time window to compensate the signal propagation delay on the connection cable.



Figure B-1: Parasitic impact of DUT connection cable propagation delay

The reference time  $t_0$  should be corrected in one of the following methods.

- a) Prepare a time delay in a TLP test system in advance and use it for correction. The adjustments derived from this way should be applied to the data within the operating system software or during post-processing using spreadsheet or other data analysis software.
- b) During the error correction open circuit methodology in 6.2.3 of the IEC 62615, determine t<sub>0</sub> from the timing when the rising edge of the voltage reflected wave becomes 10 % of its amplitude as shown in Figure B-2. The adjustment derived from this way should be applied to the data within the operating system software or during post-processing using spreadsheet or other data analysis software.
- c) During the pulse waveform measurement, trigger at the timing when the rising edge of the voltage reflection wave becomes 10 % of its amplitude and use the trigger timing as t<sub>0</sub> as shown in Figure B-3.



Figure B-2: Correction method b) for reference time  $t_0$ 



Figure B-3: Correction method c) for reference time t<sub>0</sub>

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